

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei Yamazaki et al. Art Unit : 2871
Serial No. : 09/809,646 Examiner : Thoi V. Duong
Filed : March 16, 2001 Conf. No. : 5011
Title : SEMICONDUCTOR DISPLAY DEVICE AND MANUFACTURING METHOD
THEREOF

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Supplemental to the Information Disclosure Statement (IDS) filed September 22, 2006, Applicants submit the attached corrected form PTO-1449. The corrected form PTO-1449 is being submitted to correct errors in the descriptions for references Desig. ID "CA" and "CC". The attached form PTO-1449 includes the corrected information in bold print.

No fee is believed to be due in connection with the filing of this paper on the Electronic Filing System (EFS). In the event that any fees are due, please apply any charges or credits to deposit account 06-1050.

Respectfully submitted,

Date: 12/29/06


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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12732-021001	Application No. 09/809,646
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Shunpei Yamazaki	
		Filing Date March 16, 2001	Group Art Unit 2871

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
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Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
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Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
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							Yes	No
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	CD	

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